

CMPD7000

**SURFACE MOUNT
DUAL, IN SERIES
SILICON SWITCHING DIODES**



SOT-23 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD7000 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, connected in a series configuration, designed for high speed switching applications.

MARKING CODE: C5C

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
Average Forward Current
Peak Forward Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{RRM} 100
 I_O 200
 I_{FM} 500
 P_D 350
 T_J, T_{stg} -65 to +150
 θ_{JA} 357

UNITS

V
mA
mA
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

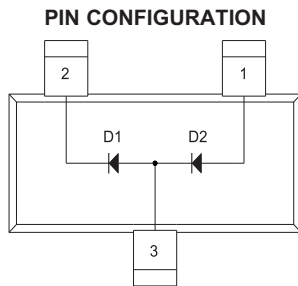
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=50\text{V}$			300	nA
I_R	$V_R=50\text{V}, T_A=125^\circ\text{C}$			100	μA
I_R	$V_R=100\text{V}$			500	nA
BV_R	$I_R=100\mu\text{A}$	100			V
V_F	$I_F=1.0\text{mA}$	0.55		0.70	V
V_F	$I_F=10\text{mA}$	0.67		0.82	V
V_F	$I_F=100\text{mA}$	0.75		1.10	V
C_T	$V_R=0, f=1.0\text{MHz}$		1.5	2.6	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		2.0	4.0	ns

R7 (27-January 2010)

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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:
 1) Anode D2
 2) Cathode D1
 3) Anode D1, Cathode D2

MARKING CODE: C5C

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R7 (27-January 2010)